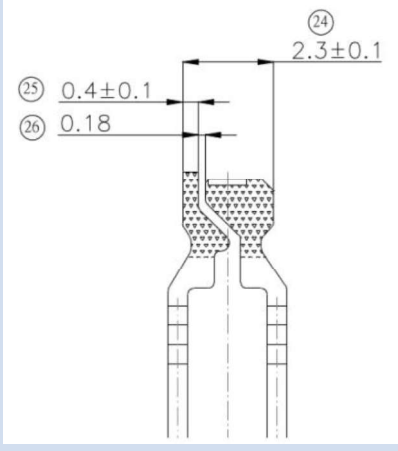
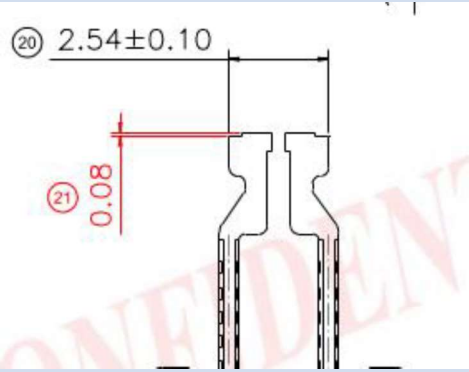
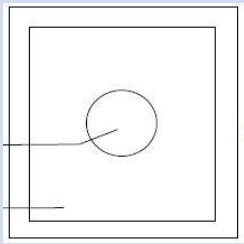


支架外觀對比外觀比較
leadframe appearance comparison

Now	After
 <p>Technical drawing of a leadframe component labeled 'Now'. It shows a cross-section of a component with three dimensions: (25) 0.4±0.1, (26) 0.18, and (24) 2.3±0.1. The drawing is a black and white line drawing with a hatched area indicating a specific material or feature.</p>	 <p>Technical drawing of a leadframe component labeled 'After'. It shows a cross-section of a component with two dimensions: (20) 2.54±0.10 and (21) 0.08. The drawing is a black and white line drawing with a hatched area indicating a specific material or feature. A red watermark 'CONFIDENTIAL' is visible across the drawing.</p>

晶片外觀對比外觀比較
chip appearance comparison

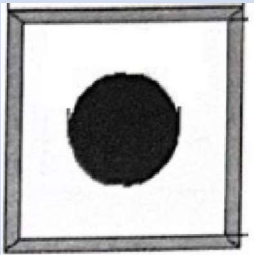
Now



photoelectricity (now)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F=20\text{ mA}$		1.82	2.00	V
Reverse Voltage	V_R	$I_R=10\text{ }\mu\text{A}$	5			V
Luminous Intensity	I_V	$I_F=20\text{ mA}$	10.0	\varnothing		mcd
Wavelength	λ_p/λ_d	$I_F=20\text{ mA}$		655/640		nm
Spectrum Width of Half Value	$\Delta\lambda$	$I_F=20\text{ mA}$		20		nm

After



photoelectricity (after)

参数	符号	条件	Min	Typ	Max	单位
正向电压	V_F	$I_F=20\text{mA}$	1.90		2.20	V
	V_R	$I_R=10\mu\text{A}$	1.30		1.60	V
反向电流	I_R	$V_F=-10\text{V}$	0		2.0	μA
主波长	λ_d	$I_F=20\text{mA}$	638		645	nm
半高宽	$\Delta\lambda$	$I_F=20\text{mA}$		20		nm
光强等级	IV	A1	14		22	mcd
		A2	19		27	
		A3	24		32	

位置position

Now	After
